

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	173820	(semiconductor near substrate)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2004/12/12 19:38
L2	25630	(cleaning adj process)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2004/12/12 19:59
L3	19	annealling adj process	US-PGPUB; USPAT; EPO; JPO	OR	ON	2004/12/12 19:39
L4	0	hydrogen near1 annealling	US-PGPUB; USPAT; EPO; JPO	OR	ON	2004/12/12 19:39
L5	2	hydrogen near1 annealling	US-PGPUB; USPAT; EPO; JPO	OR	ON	2004/12/12 19:40
L6	5	hydrogen with annealling	US-PGPUB; USPAT; EPO; JPO	OR	ON	2004/12/12 19:40
L7	7171	hydrogen with anneal\$4	US-PGPUB; USPAT; EPO; JPO	OR	ON	2004/12/12 19:40
L8	12252	nitrid\$5 near3 process	US-PGPUB; USPAT; EPO; JPO	OR	ON	2004/12/12 19:42
L9	168814	thermal\$2 with (process treating treatment)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2004/12/12 19:42
L10	1	1 same 2 same 7 same 8 same 9	US-PGPUB; USPAT; EPO; JPO	OR	ON	2004/12/12 19:43
L11	22	1 and 2 and 7 and 8 and 9	US-PGPUB; USPAT; EPO; JPO	OR	ON	2004/12/12 19:46
L12	10	1 with 2 with remov\$3 with (natural near1 oxide)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2004/12/12 20:02
L13	23	("5509970").URPN.	USPAT	OR	ON	2004/12/12 19:52
L14	6	("4264374"   "4778532"   "5129955"   "5221423"   "5290361"   "5308400").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2004/12/12 19:55
L15	30142	(cleaning near1 (process rca))	US-PGPUB; USPAT; EPO; JPO	OR	ON	2004/12/12 20:00
L16	30188	(cleaning near1 process) (rca near1 (process cleaning))	US-PGPUB; USPAT; EPO; JPO	OR	ON	2004/12/12 20:01

L17	373613	1 wafer	US-PGPUB; USPAT; EPO; JPO	OR	ON	2004/12/12 20:01
L18	8894	16 and 17	US-PGPUB; USPAT; EPO; JPO	OR	ON	2004/12/12 20:01
L19	268	18 and 7	US-PGPUB; USPAT; EPO; JPO	OR	ON	2004/12/12 20:02
L20	78	19 and (gate near oxide)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2004/12/12 20:02
L21	19	20 and 8	US-PGPUB; USPAT; EPO; JPO	OR	ON	2004/12/12 20:07
L22	2	21 and (remov\$3 with (natural near1 oxide))	US-PGPUB; USPAT; EPO; JPO	OR	ON	2004/12/12 20:19
L23	20	"6008128"	US-PGPUB; USPAT; EPO; JPO	OR	ON	2004/12/12 20:07
L24	1	"6124218"	US-PGPUB; USPAT; EPO; JPO	OR	ON	2004/12/12 20:07
L25	3	"6391796"	US-PGPUB; USPAT; EPO; JPO	OR	ON	2004/12/12 20:07
L26	1	"20020036324"	US-PGPUB; USPAT; EPO; JPO	OR	ON	2004/12/12 20:07
L27	22	23 24 25 26	US-PGPUB; USPAT; EPO; JPO	OR	ON	2004/12/12 20:08
L28	2	27 and (remov\$3 with (natural near1 oxide))	US-PGPUB; USPAT; EPO; JPO	OR	ON	2004/12/12 20:08
L29	2	11 and (remov\$3 with (natural near1 oxide))	US-PGPUB; USPAT; EPO; JPO	OR	ON	2004/12/12 20:22
L30	0	"5656516".pn. and (gate near oxide)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2004/12/12 20:22